



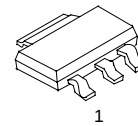
PZT4033

PNP SILICON TRANSISTOR

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DESCRIPTION

The UTC PZT4033 designed for high current general purpose amplifier applications.



SOT-223

*Pb-free plating product number:PZT4033L

ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
PZT4033-AA3-R	PZT4033L-AA3-R	SOT-223	B	C	E	Tape Reel

PZT4033L-AA3-R (1)Packing Type (2)Package Type (3)Lead Plating	(1) R: Tape Reel (2) AA3: SOT-223 (3) L: Lead Free Plating, Blank: Pb/Sn
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■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Power Dissipation	P_D	2	W
Collector Current	I_C	-1	A
Junction Temperature	T_J	-65 ~ +150	°C
Storage Temperature	T_{STG}	-65 ~ +150	

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

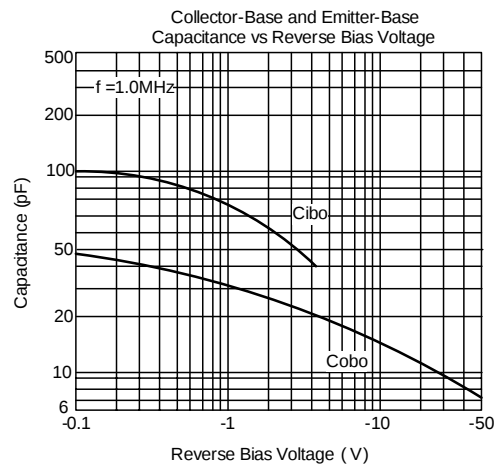
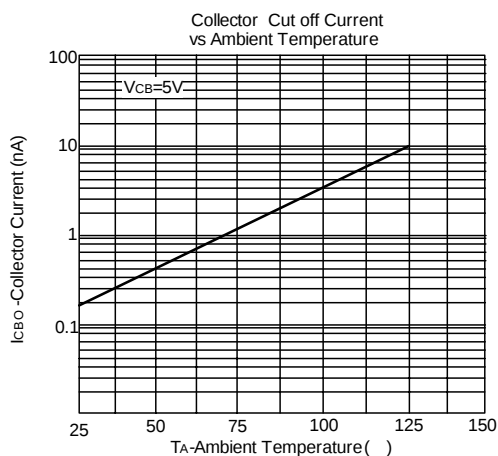
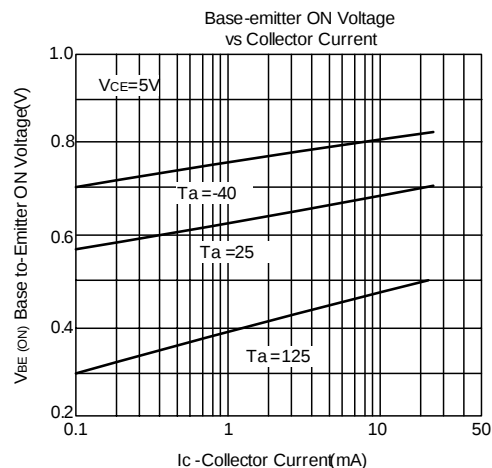
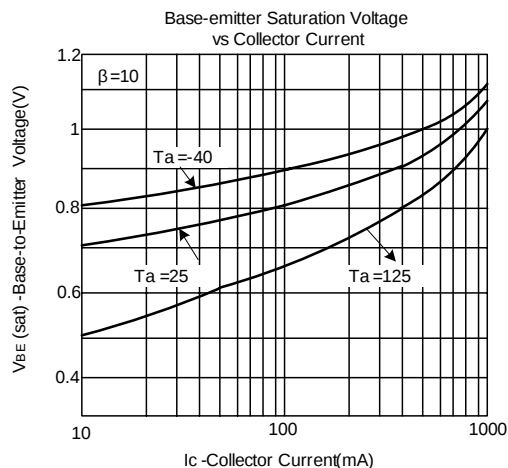
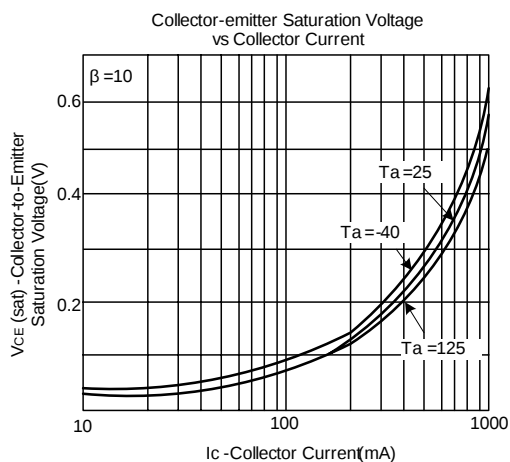
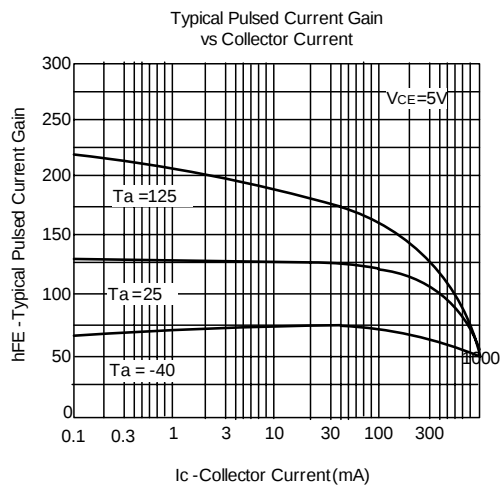
■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Thermal Resistance	θ_{JA}	62.5	°C/W

■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = -10\mu A, I_E = 0$	-80			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -10mA, I_B = 0$	-80			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -60V, I_E = 0$			-50	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-10	nA
DC Current Gain	h_{FE}	$V_{CE} = -5V, I_C = -0.1mA$ $V_{CE} = -5V, I_C = -100mA$ $V_{CE} = -5V, I_C = -500mA$ $V_{CE} = -5V, I_C = -1A$	75 100 70 25		300	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -150mA, I_B = -15mA$ $I_C = -500mA, I_B = -50mA$			-0.15 -0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = -150mA, I_B = -15mA$ $I_C = -500mA, I_B = -50mA$			-0.9 -1.1	V
Gain Bandwidth Product	f	$V_{CE} = -10V, I_C = -50mA, f = 1MHz$	100			MHz
Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			20	pF
Input Capacitance	C_{ib}	$V_{EB} = -0.5V, I_C = 0, f = 1MHz$			110	pF
Switching Time	Turn-on Time	$I_C = -500mA, V_{CE} = -30V,$ $I_{B1} = -I_{B2} = -50mA$			100	ns
	Storage Time				350	ns
	Fall Time				50	ns

TYPICAL CHARACTERISTICS



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